OIPE
FEB 17 2005
PATENT & TRADEMARK OFFICE

Docket No. F03-367-USDIV
FUJIT.045DIV2A

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re divisional patent application of 10/391,648 filed on March 20, 2003

Norikatsu KOIDE

Serial No.:	Not Yet Assigned	Group Art Unit:	Not Yet Assigned
Filing Date:	Concurrently Herewith	Examiner:	Unknown

For: METHOD FOR MANUFACTURING GALLIUM NITRIDE GROUP COMPOUND SEMICONDUCTOR

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT LETTER CITING APPLICATIONS

Sir:

The Examiner's attention is directed to the following applications of:

Examiner's Initials	FIRST INVENTOR (Last Name Only)	APPLICATION NO. and Filing Date	ENCLOSED
	KOIKE	09/566,917, May 9, 2000	Specification, Drawings, Current Claims

PLEASE DO NOT PRINT the above information on the patent which results from the subject application.

Consideration of each listed application is earnestly solicited since unpublished patent applications are contemplated as Information Disclosure Statement material; see the exception in Rule 98(a)(2)(iii) and note the penultimate sentence of MPEP 609.

Further, in keeping with MPEP 609, Subsection C(2), 2nd paragraph, line 10 to end of the paragraph (especially note lines 18-25), **PLEASE RETURN A COPY OF THIS LETTER** with the Examiner's initials adjacent each above listing so that applicant will know that each listed application has been considered as required by PTO policy.

Copies of these applications are not provided in accordance with 37 C.F.R. §1.98(d), as they were cited in the parent Application.

This citation does not constitute an admission that the references are relevant or material to the claims. They are only cited as constituting related art of which the applicant is aware.

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

OIPE JC11
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ATTY DOCKET NO.	SERIAL NO.
F03-367-US div	Not Yet Assigned
APPLICANT(S)	
Norikatsu Koide	
FILING DATE	GROUP
Concurrently Herewith	Not Yet Assigned

PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
		8-274411	10/18/96	JAPAN				
		8-116090	05/07/96	JAPAN				
		5-283744	10/29/93	JAPAN				
		4-303920	10/27/92	JAPAN				
		9-162125	06/20/97	JAPAN				

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

			Partial Translation of Japanese Patent Application No. 9-311518 dated June 10, 2003.
			D. Kapolnek et al., "Anisotropic epitaxial lateral growth in GaN selective area epitaxy", Appl. Phys. Lett. 71 (9), September 1, 1997, pp. 1204-1206.

EXAMINER	DATE CONSIDERED

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OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

		Hidetada Matsushima et al., "Selective growth of GaN on sub-micron pattern by MOVPE", Technical Report of IEICE, pp. 41-46.
		Yoshinori Ujiie et al., "Epitaxial Lateral Overgrowth of GaAs on a Si Substrate", Japanese Journal of Applied Physics, Vol. 28, No. 3, March, 1989, pp. L337-L339.

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		11-043398						
		11-135832						
		11-135770						
		11-274082						
		2000-174393						

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		6,051,849	04/18/00	Davis et al.			
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		6,146,457	11/14/00	Solomon			
		5,798,536	08/25/98	Tsutsui			
		5,185,290	02/09/93	Aoyagi et al.			
		6,153,010	11/28/00	Kiyoku et al.			
		6,110,277	08/29/00	Braun			

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		PCT WO 00/04615	01/27/00	WIPO				
		2000-150959	05/30/00	JAPAN				
		2000-261106	09/22/00	JAPAN				
		8-64791	03/08/96	JAPAN				
		7-273367	10/20/95	JAPAN				

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			Akasaki et al., "Effects of AlN Buffer Layer on Crystallographic Structure and on Electrical and Optical Properties of GaN and Ga1-xA1xN...Movpe", pp. 209-219, Journal of Crystal Growth 98 (1989) North-Holland, Amsterdam.
			Yang et al., "High Quality GaN-InGaN heterostructures grown on (111) silicon substrates", pp. 3566-3568, Appl. Phys. Lett. 69 (23), December 2, 1996.

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		2000-106473	04/11/00	JAPAN				
		2000-357663	12/26/00	JAPAN				
		2001-176813	06/29/01	JAPAN				

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			Wolf et al., for the VLSI Era, Volume 1 - Process Technology, page 5, "Silicon: Single Crystal Growth and Wafer Preparation."
			Hiramatsu et al., "Selective area growth and epitaxial lateral overgrowth of GaN by metalorganic vapor phase epitaxy and hydride vapor phase epitaxy", pp. 104-111, Materials Science and Engineering B59 (1999).

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		05-041536	02/19/93	JAPAN				
		04-084418	03/17/92	JAPAN				
		EP 0 551 721 A2	11/12/92	EUROPE			✓	

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		EP 0 951 055 A2	11/10/98	EUROPE			✓	
		EP 1 059 677 A2	12/13/00	EUROPE			✓	
		EP 1 059 661 A2	12/13/00	EUROPE			✓	
		EP 1 045 431 A1	10/18/00	EUROPE			✓	
		EP 0 779 666 A3	06/18/97	EUROPE			✓	

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		PCT WO 02/058120 A1	07/25/02	EUROPE			✓	
		PCT WO 99/01594	01/14/99	EUROPE			✓	

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

			PCT Form 210 (PCT/JP02/05446)
			PCT Form 210 (PCT/JP02/02628)

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*EXAMINER INITIAL		OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*
		PCT Form 210 (PCT/JP02/01159) ✓
		PCT Form 210 (PCT/JP01/01928) ✓
		PCT Form 210 (PCT/JP01/02695) ✓
		PCT Form 210 (PCT/JP00/09120)
		PCT Form 210 (PCT/JP01/01396)
		PCT Form 210 (PCT/JP01/01178)
		PCT Form 210 (PCT/JP01/01663)
		PCT Form 210 (PCT/JP00/09121)
		PCT Form 210 (PCT/JP00/09220)
		PCT Forms 338 and 409 (IPER) (PCT/JP01/02695) and translations. ✓
		PCT Forms 338 and 409 (IPER) (PCT/JP01/01663) and translations
		PCT Forms 338 and 409 (IPER) (PCT/JP00/09120) and translations

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*EXAMINER INITIAL		OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*
		PCT Forms 338 and 409 (PCT/JP01/01928) and translations thereof
		PCT Forms 338 and 409 (PCT/JP01/01396) and translations thereof
		EP 27057 dated 07/18/00 (EUROPE)
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		PCT Forms 338 and 409 (IPER) (PCT/JP00/09121) and translations
		Wolf et al., "SILICON PROCESSING for the VLSI Era," Vol. 1, Page 5, Lattice Press, 1986.

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		5-343741	12/1993	JAPAN				
		97-11518	03/1997	PCT				
		98/47170	10/1998	PCT				
		03024719	02/1991	JAPAN				
		11-191659	07/1999	JAPAN				

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		11-191657	07/1999	JAPAN				
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		4-10665	01/1992	JAPAN				
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		8-222812	08/1996	JAPAN				

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			Zheleva et al., "Pendeo-Epitaxy - A New Approach for Lateral Growth of Gallium Nitride Structures", MRS Internet J. Nitride Semicond. Res. 4S1, G3.38 (1999).
			Dimitriadis et al., "Contacts of Titanium Nitride to n- and p-type Gallium Nitride Films", Solid State Electronics Vol. 43, (1999), pp. 1969-1972.

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			Uchida et al., "AlGaInN Based Laser Diodes", III-Vs Review: Covering Advanced Semiconductors Worldwide, Vol. 13, No. 3, May/June 2000, pp. 156-164.

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		2000-091253	03/2000	JAPAN				
		2001-060719	03/2001	JAPAN				
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		EP 0 993 048 A2	04/2000	EUROPE				
		WO 00/55893	09/2000	WIPO				
		WO 97/11518	03/1997	WIPO				

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		6,121,121	09/2000	KOIDE			
		5,239,188 A	08/1993	Takeuchi et al.			

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
		WO 98/47170	10/1998	WIPO				
		11-145516	05/1999	JAPAN				

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

EXAMINER	DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)	Application Number
F03-367-US DIV	Not Yet Assigned
Applicant(s)	
Norikatsu Koide	
Filing Date	**Group Art Unit**
Concurrently Herewith	Not Yet Assigned

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		6,617,668	09/09/03	Koide et al.			
		6,518,599	08/16/01	Umezaki et al.			

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

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